

Amendments to the Claims

Claim 1-53 (cancelled).

Claim 54 (previously presented): A method for removing organic materials, comprising removing at least a portion of an organic-material-comprising layer from a barrier material surface with a pad and a fluid, the fluid being substantially unreactive with the surface and comprising less than or equal to about 0.1 weight percent particles at an initiation of the removing.

Claim 55 (previously presented): The method of claim 54 wherein the organic-material-comprising layer comprises one or more of photoresist, non-photosensitive resist, and polyimide.

Claim 56 (previously presented): The method of claim 54 wherein a pH of the fluid is from about 8 to about 12.

Claim 57 (previously presented): The method of claim 54 wherein the fluid comprises one or both of ammonia and TMAH.

Claim 58 (previously presented): The method of claim 54 wherein the fluid comprises water.

Claim 59-61 (cancelled).

Claim 62 (previously presented): The method of claim 54 wherein the barrier material comprises one or both of tantalum silicon nitride and tantalum nitride.

Claim 63 (previously presented): The method of claim 54 wherein the pad comprises polyurethane.

Claim 64 (previously presented): A method for removing organic materials, comprising removing at least a portion of an organic-material-comprising layer from a semiconductive substrate surface with a pad and a fluid, the fluid being substantially unreactive with the surface and comprising less than or equal to about 0.1 weight percent particles at an initiation of the removing, wherein at least some of the particles comprise silica.

Claim 65 (previously presented): A method for removing organic materials, comprising removing at least a portion of an organic-material-comprising layer from a semiconductive substrate surface with a pad and a fluid, the fluid being substantially unreactive with the surface and comprising less than or equal to about 0.1 weight percent particles at an initiation of the removing, wherein the surface comprises at least two layers, a first conductive layer of the two layers comprising N and Si, and a second conductive layer of the two layers comprising N.

Claim 66-73 (cancelled).

Claim 74 (previously presented): A material removal method comprising:

providing a substrate supporting a barrier-material-comprising layer, the barrier-material-comprising layer having an organic-material-comprising layer thereover; selectively removing at least a portion of the organic-material-comprising layer with a first polishing process utilizing a first liquid to thereby expose at least a portion of an upper surface of the barrier-material-comprising layer, wherein the first liquid is substantially unreactive with the barrier-material-comprising layer and comprises less than or equal to 0.1 weight percent particles at an initiation of the removing; and removing at least a portion of the barrier-material-comprising layer with a second polishing process utilizing a second liquid.

Claim 75 (cancelled).

Claim 76 (previously presented): The method of claim 74 wherein the organic-material-comprising layer comprises one or more of photoresist, non-photosensitive resist and polyimide.

Claim 77 (previously presented): The method of claim 74 wherein the first polishing process comprises removing at least a portion of the organic-material-comprising layer with a chemical mechanical polishing pad and the first liquid.

Claim 78 (previously presented): The method of claim 77 wherein the second polishing process comprises removing at least a portion of the barrier-material-comprising layer with the chemical mechanical polishing pad and the second liquid.

Claim 79 (previously presented): The method of claim 74 wherein the first liquid comprises water.

Claim 80 (previously presented): The method of claim 74 wherein the first liquid comprises one or both of ammonia and TMAH.

Claim 81 (previously presented): The method of claim 74 wherein the second liquid comprises less than or equal to approximately 0.1 weight percent particles at an initiation of the removing of the barrier-material-comprising layer.

Claim 82 (previously presented): The method of claim 74 wherein the second liquid comprises particles.

Claim 83 (previously presented): The method of claim 74 wherein a composition of the second liquid is different than a composition of the first liquid.

Claim 84 (previously presented): A material removal method comprising:

providing a substrate supporting a conductive-material-comprising layer, the conductive-material-comprising layer having an organic-material-comprising layer thereover;

selectively removing at least a portion of the organic-material-comprising layer with a first polishing process utilizing a first liquid to thereby expose at least a portion of an upper surface of the conductive-material-comprising layer, wherein the first liquid is substantially unreactive with the conductive-material-comprising layer and comprises less than or equal to 0.1 weight percent particles at an initiation of the removing; and

removing at least a portion of the conductive-material-comprising layer with a second polishing process utilizing a second liquid, wherein the second liquid is reactive with the conductive-material-comprising layer.

Claim 85 (cancelled).

Claim 86 (previously presented): The method of claim 74 wherein the barrier-material-comprising layer comprises one or both of tantalum silicon nitride and tantalum nitride.

Claim 87 (previously presented): The method of claim 64 wherein the surface comprises a conductive material.

Claim 88 (previously presented): The method of claim 87 wherein the conductive material comprises one or more of platinum, iridium, ruthenium, and tantalum.

Claim 89 (previously presented): The method of claim 65 wherein the organic-material-comprising layer comprises one or more of photoresist, non-photosensitive resist, and polyimide.

Claim 90 (previously presented): The method of claim 65 wherein a pH of the fluid is from about 8 to about 12.

Claim 91 (previously presented): The method of claim 65 wherein the fluid comprises one or both of ammonia and TMAH.

Claim 92 (previously presented): The method of claim 65 wherein the fluid comprises water.

Claim 93 (previously presented): The method of claim 65 wherein the pad comprises polyurethane.

Claim 94 (previously presented): The method of claim 84 wherein the conductive-material-comprising layer comprises one or more of platinum, iridium, ruthenium, and tantalum.

Claim 95 (previously presented): The method of claim 84 wherein the organic-material-comprising layer comprises one or more of photoresist, non-photosensitive resist and polyimide.

Claim 96 (previously presented): The method of claim 84 wherein the first polishing process comprises removing at least a portion of the organic-material-comprising layer with a chemical mechanical polishing pad and the first liquid.

Claim 97 (previously presented): The method of claim 96 wherein the second polishing process comprises removing at least a portion of the conductive-material-comprising layer with the chemical mechanical polishing pad and the second liquid.

Claim 98 (previously presented): The method of claim 84 wherein the first liquid comprises water.

Claim 99 (previously presented): The method of claim 84 wherein the first liquid comprises one or both of ammonia and TMAH.

Claim 100 (previously presented): The method of claim 84 wherein the second liquid comprises less than or equal to approximately 0.1 weight percent particles at an initiation of the removing of the conductive-material-comprising layer.

Claim 101 (previously presented): The method of claim 84 wherein a composition of the second liquid is different than a composition of the first liquid.

Claim 102 (previously presented): The method of claim 84 wherein the second liquid comprises particles.